

Kirstin Alberi

List of Publications by Year in descending order

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25
papers

548
citations

933447

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h-index

839539

18
g-index

25
all docs

25
docs citations

25
times ranked

1089
citing authors

#	ARTICLE	IF	CITATIONS
1	High Mobility Cd ₃ As ₂ (112) on GaAs(001) Substrates Grown via Molecular Beam Epitaxy. ACS Applied Electronic Materials, 2022, 4, 729-734.	4.3	4
2	Epitaxial Dirac Semimetal Vertical Heterostructures for Advanced Device Architectures. Advanced Functional Materials, 2022, 32, .	14.9	11
3	Quantitative orderâ€parameter measurement in latticeâ€mismatched AlInP using precession electron diffraction. Journal of Microscopy, 2021, 284, 132-141.	1.8	0
4	The 2019 materials by design roadmap. Journal Physics D: Applied Physics, 2019, 52, 013001.	2.8	236
5	Experimental demonstration of voltage-matched two-terminal tandem minimodules. Journal of Photonics for Energy, 2019, 8, 1.	1.3	3
6	Controlling ZnSe/GaAs interface properties: The role of elemental exposure and photon irradiation during growth initiation. Journal of Applied Physics, 2018, 124, .	2.5	4
7	Effects of excess carriers on charged defect concentrations in wide bandgap semiconductors. Journal of Applied Physics, 2018, 123, .	2.5	7
8	Low-Cost CdTe/Silicon Tandem Solar Cells. IEEE Journal of Photovoltaics, 2017, 7, 1767-1772.	2.5	26
9	Tailoring Heterovalent Interface Formation with Light. Scientific Reports, 2017, 7, 8516.	3.3	10
10	Demonstration of GaInP ₂ /Si Voltage Matched Tandem Solar Cells. , 2017, , .		4
11	Simulated potential for enhanced performance of mechanically stacked hybrid IIIâ€V/Si tandem photovoltaic modules using DCâ€DC converters. Journal of Photonics for Energy, 2017, 7, 1.	1.3	12
12	Spectroscopic determination of the bandgap crossover composition in MBE-grown Al _x Ga _{1-x} As. Japanese Journal of Applied Physics, 2015, 54, 042402.	1.5	4
13	Amber-green light-emitting diodes using order-disorder Al _x In _{1-x} P heterostructures. Journal of Applied Physics, 2013, 114, .	2.5	30
14	Dislocation-limited open circuit voltage in film crystal silicon solar cells. Applied Physics Letters, 2012, 101, 123510.	3.3	6
15	Heteroepitaxial film crystal silicon on Al ₂ O ₃ : new route to inexpensive crystal silicon photovoltaics. Energy and Environmental Science, 2011, 4, 3346.	30.8	33
16	Hot-wire chemical vapor deposition of epitaxial film crystal silicon for photovoltaics. Thin Solid Films, 2011, 519, 4545-4550.	1.8	38
17	Light trapping by a dielectric nanoparticle back reflector in film silicon solar cells. Applied Physics Letters, 2011, 99, 064101.	3.3	34
18	On the bandgap of hydrogenated nanocrystalline silicon thin films. , 2010, , .		6

#	ARTICLE	IF	CITATIONS
19	Material quality requirements for efficient epitaxial film silicon solar cells. Applied Physics Letters, 2010, 96, 073502.	3.3	43
20	Mechanisms controlling the phase and dislocation density in epitaxial silicon films grown from silane below 800°C. Applied Physics Letters, 2010, 96, .	3.3	23
21	Photovoltaic device characterization with optical second harmonic generation. , 2010, , .		1
22	Photovoltaic-quality silicon epitaxy by hot-wire CVD at glasscompatible temperatures. , 2009, , .		0
23	Epitaxial film silicon solar cells fabricated by hot wire chemical vapor deposition below 750°C. , 2009, , .		0
24	Composition dependence of Schottky barrier heights and bandgap energies of GaN _x As _{1-x} synthesized by ion implantation and pulsed-laser melting. Journal of Applied Physics, 2008, 104, .	2.5	11
25	Design and Demonstration of Al _x In _{1-x} P Multiple Quantum Well Light-Emitting Diodes. Journal Physics D: Applied Physics, 0, , .	2.8	2